

TVS Diode

Transient Voltage Suppressor Diodes

ESD203-B1-02 Series

Bi-directional ESD / Transient / Surge Protection Diodes

ESD203-B1-02ELS
ESD203-B1-02EL

Data Sheet

Revision 1.3, 2013-12-19
Final

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Page or Item	Subjects (major changes since previous revision)
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Revision 1.3, 2013-12-19

5	Update of Table 2-2)

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Last Trademarks Update 2010-10-26

1 Bi-directional ESD / Transient / Surge Protection Diodes

1.1 Features

- ESD/Transient/Surge protection of one data / V_{bus} line exceeding standard:
 - IEC61000-4-2 (ESD): ± 30 kV (air/contact discharge)
 - IEC61000-4-4 (EFT): ± 50 A (5/50 ns)
 - IEC61000-4-5 (surge): ± 5 A (8/20 μ s)
- Bi-directional symmetrical working voltage: $V_{RWM} = \pm 13.2$ V
- Low capacitance: $C_L = 6$ pF (typ.)
- Very low ESD clamping voltage, very low dynamic resistance: $R_{dyn} = 0.29 \Omega$ (typ.)
- Pb-free (RoHS compliant) and halogen free package



1.2 Application Examples

- ESD protection of keypad, touchpad, buttons, audio lines, ect.

1.3 Product Description

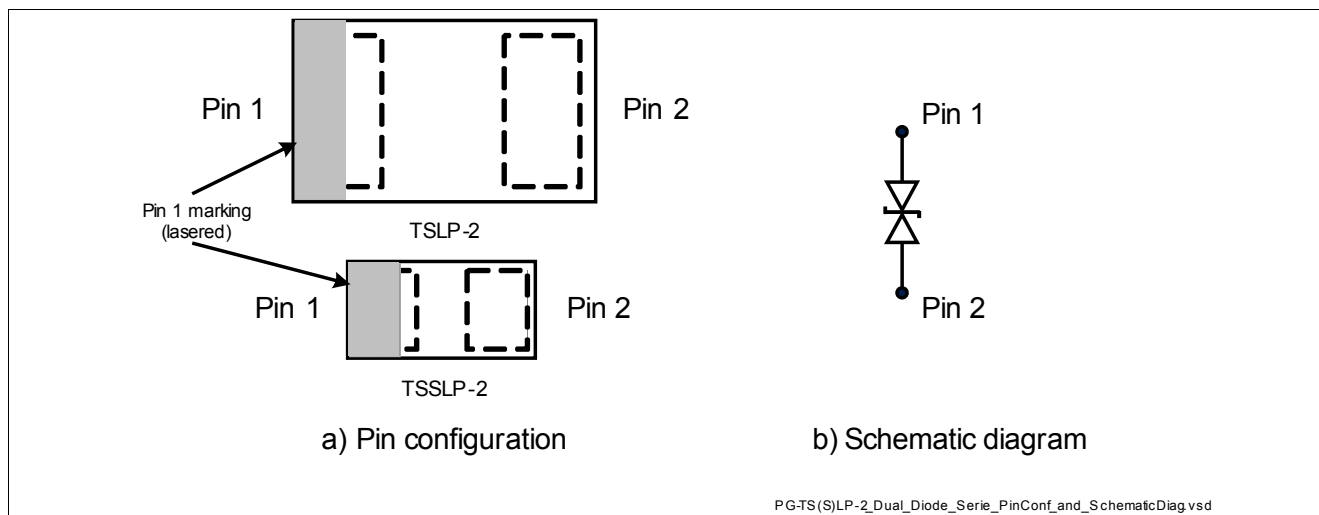


Figure 1-1 Pin Configuration and Schematic Diagram

Table 1-1 Ordering Information

Type	Package	Configuration	Marking code
ESD203-B1-02ELS	TSSLP-2-4	1 line, bi-directional	<u>H</u>
ESD203-B1-02EL	TSLP-2-20	1 line, bi-directional	H

2 Characteristics

2.1 Maximum Ratings

Table 2-1 Maximum Ratings at $T_A = 25\text{ °C}$, unless otherwise specified¹⁾

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
ESD ²⁾ air / contact discharge	V_{ESD}	-	-	30	kV
Peak pulse current ($t_p = 8/20\text{ }\mu\text{s}$) ³⁾	I_{PP}	-	-	5	A
Peak pulse power ($t_p = 8/20\text{ }\mu\text{s}$) ³⁾	P_{PK}	-	-	115	W
Operating temperature range	T_{OP}	-55	-	125	°C
Storage temperature	T_{stg}	-65	-	150	°C

1) Device is electrically symmetrical

2) V_{ESD} according to IEC61000-4-2

3) I_{PP} according to IEC61000-4-5

Attention: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

2.2 Electrical Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified

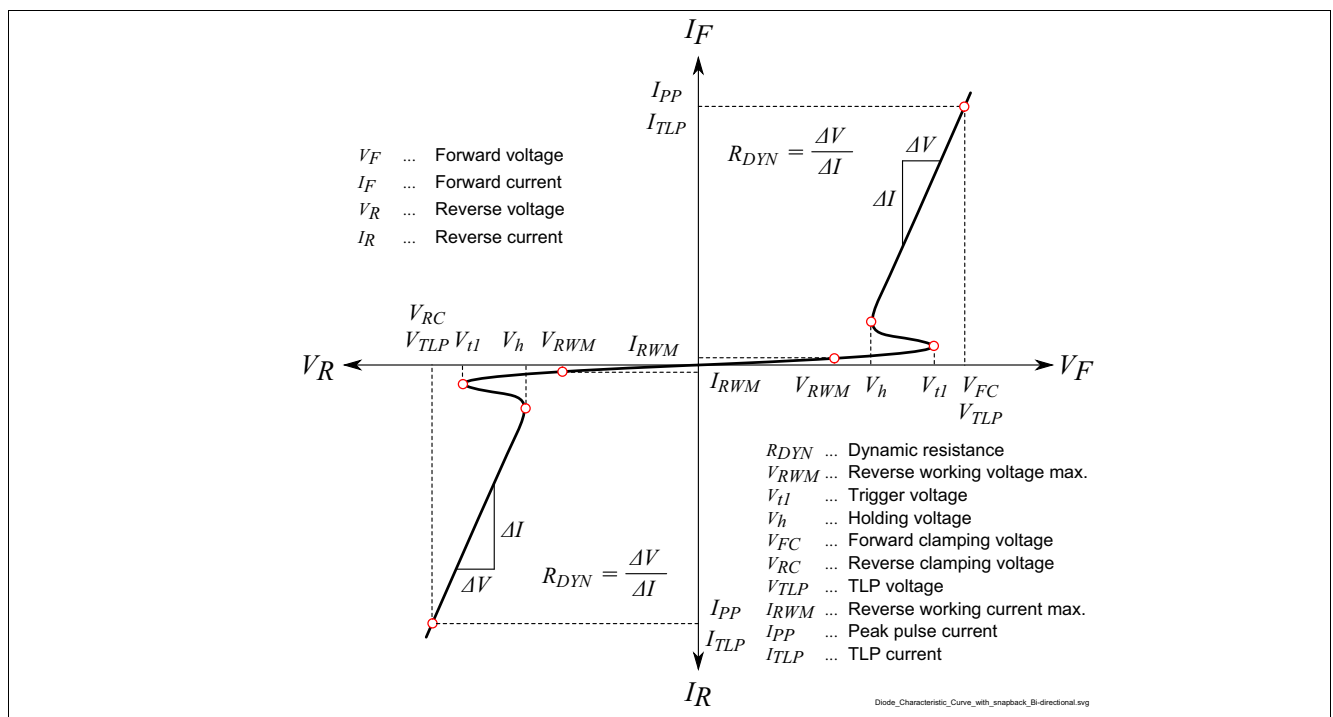


Figure 2-1 Definitions of electrical characteristics

Characteristics

Table 2-2 DC Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Reverse working voltage	V_{RWM}	-	-	13.2	V	
Reverse current	I_R	-	1	50	nA	$V_R = 12\text{ V}$
Trigger voltage	V_{t1}	13.7	-	-	V	
Holding voltage	V_h	13.7	16	-	V	$I_R = 10\text{ mA}$

1) Device is electrically symmetrical

Table 2-3 AC Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Line capacitance	C_L	-	6	9	pF	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$

Table 2-4 ESD and Surge Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clamping voltage ¹⁾	V _{CL}	-	17	-	V	I _{TLP} = 16 A
		-	23	-		I _{TLP} = 30 A
Clamping voltage ²⁾		-	17	-		I _{PP} = 1 A
		-	20	23		I _{PP} = 5 A
Dynamic resistance ¹⁾	R _{DYN}	-	0.29	-	Ω	

1) ANSI/ESD STM5.5.1 - Electrostatic Discharge Sensitive Testing using Transmission Line Pulse (TLP) Model. TLP conditions: $Z_0 = 50\text{ }\Omega$, $t_p = 100\text{ ns}$, $t_r = 0.6\text{ ns}$, I_{TLP} and V_{TLP} averaging window: $t_1 = 30\text{ ns}$ to $t_2 = 60\text{ ns}$, extraction of dynamic resistance using least squares fit of TLP characteristic between $I_{TLP1} = 5\text{ A}$ and $I_{TLP2} = 40\text{ A}$. Please refer to Application Note AN210[1]

2) I_{PP} according to IEC61000-4-5 ($t_p = 8/20\text{ }\mu\text{s}$)

Typical Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

3 Typical Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

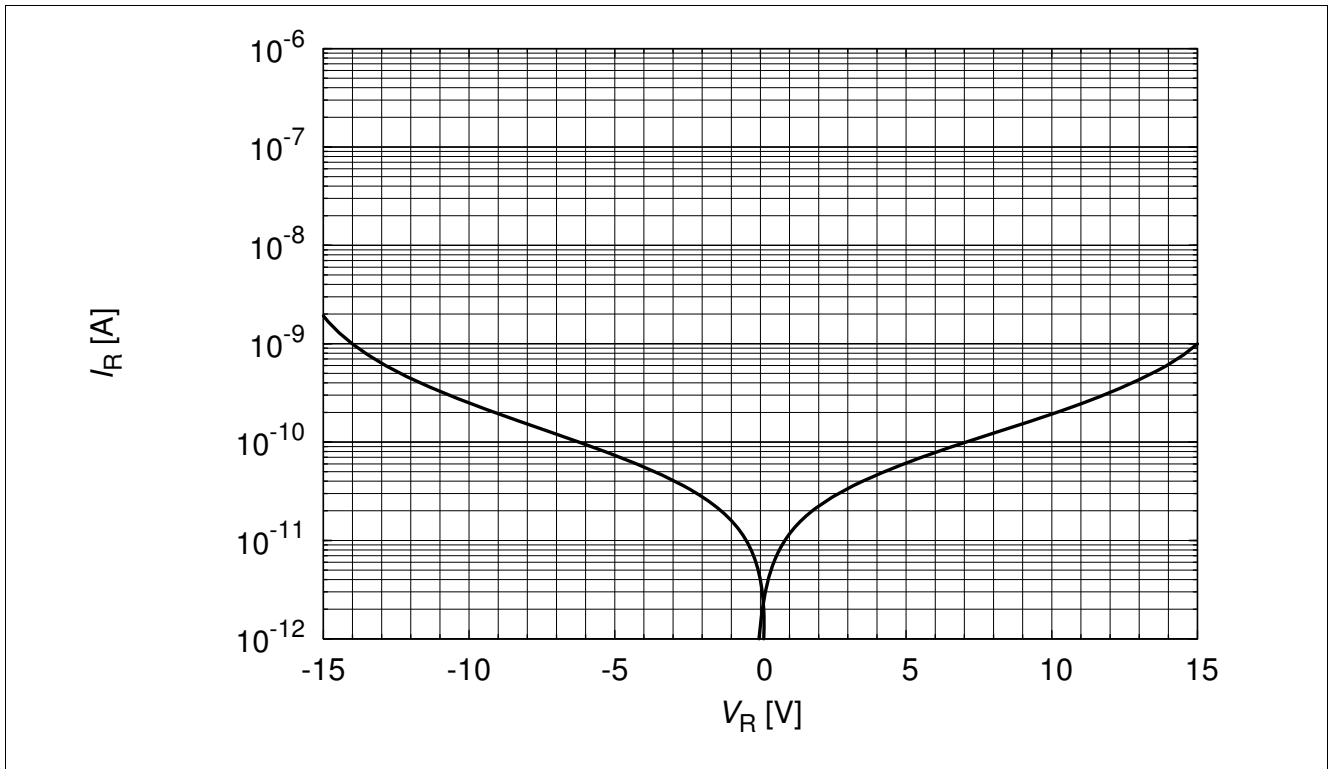


Figure 3-1 Reverse current: $I_R = f(V_R)$

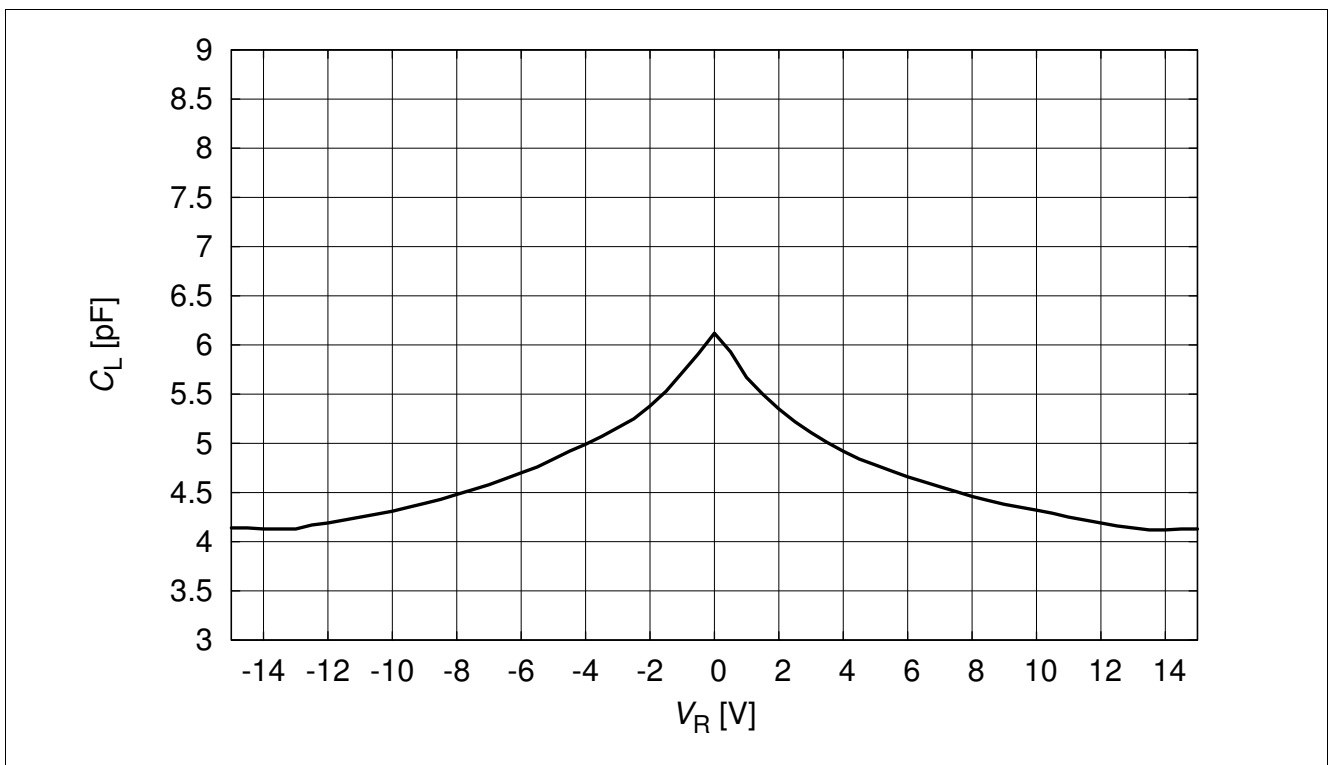


Figure 3-2 Line capacitance: $C_L = f(V_R)$, $f = 1\text{ MHz}$

Typical Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

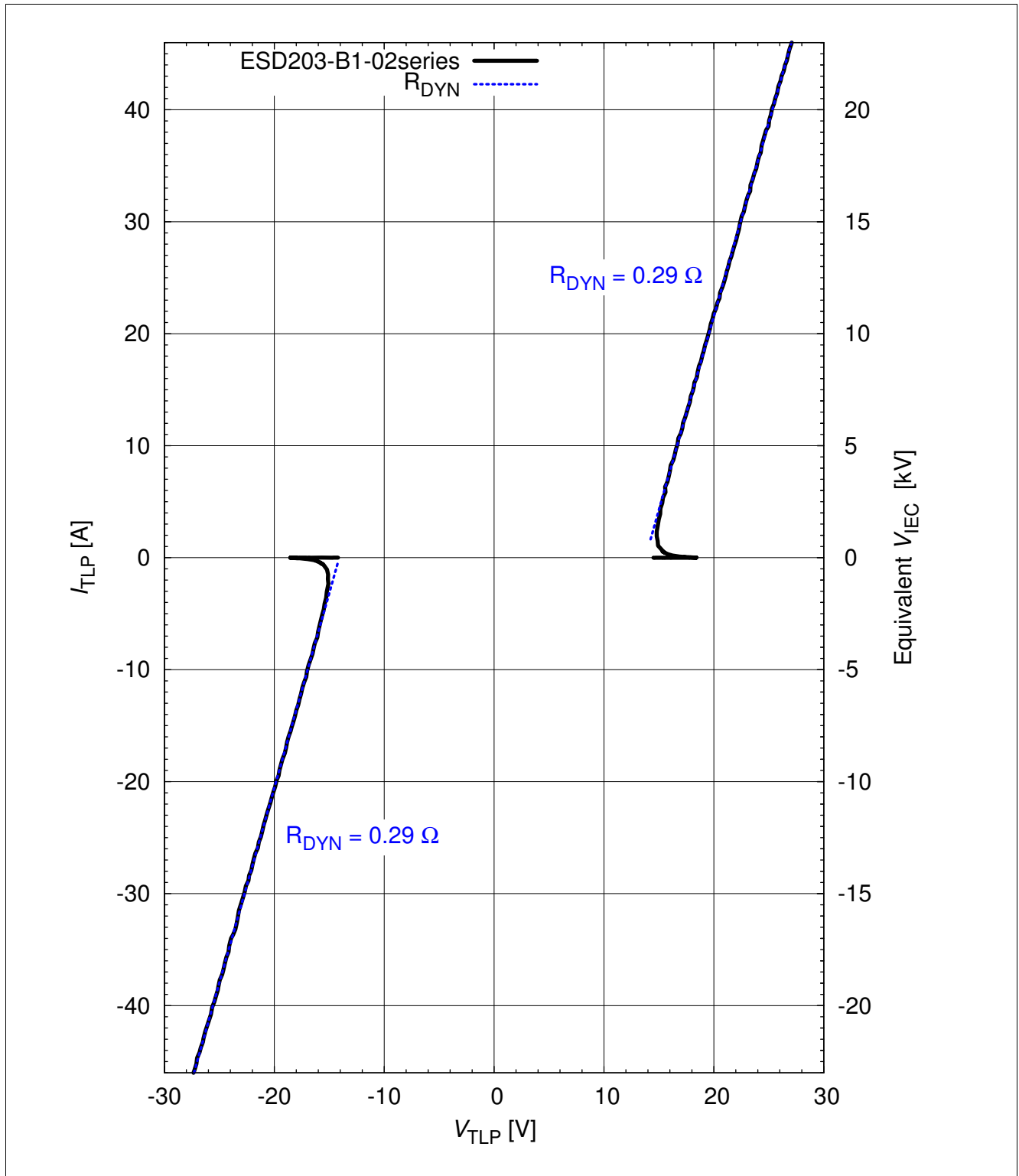


Figure 3-3 Clamping voltage (TLP): $I_{TLP} = f(V_{TLP})$ according ANSI/ESD STM5.5.1 - Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model. TLP conditions: $Z_0 = 50\text{ }\Omega$, $t_p = 100\text{ ns}$, $t_r = 0.6\text{ ns}$, I_{TLP} and V_{TLP} averaging window: $t_1 = \text{ns}$ to $t_2 = 60\text{ ns}$, extraction of dynamic resistance using squares fit to TLP characteristics between $I_{TLP1} = 5\text{ A}$ and $I_{TLP2} = 40\text{ A}$. Please refer to Application Note AN210 [1]

Typical Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

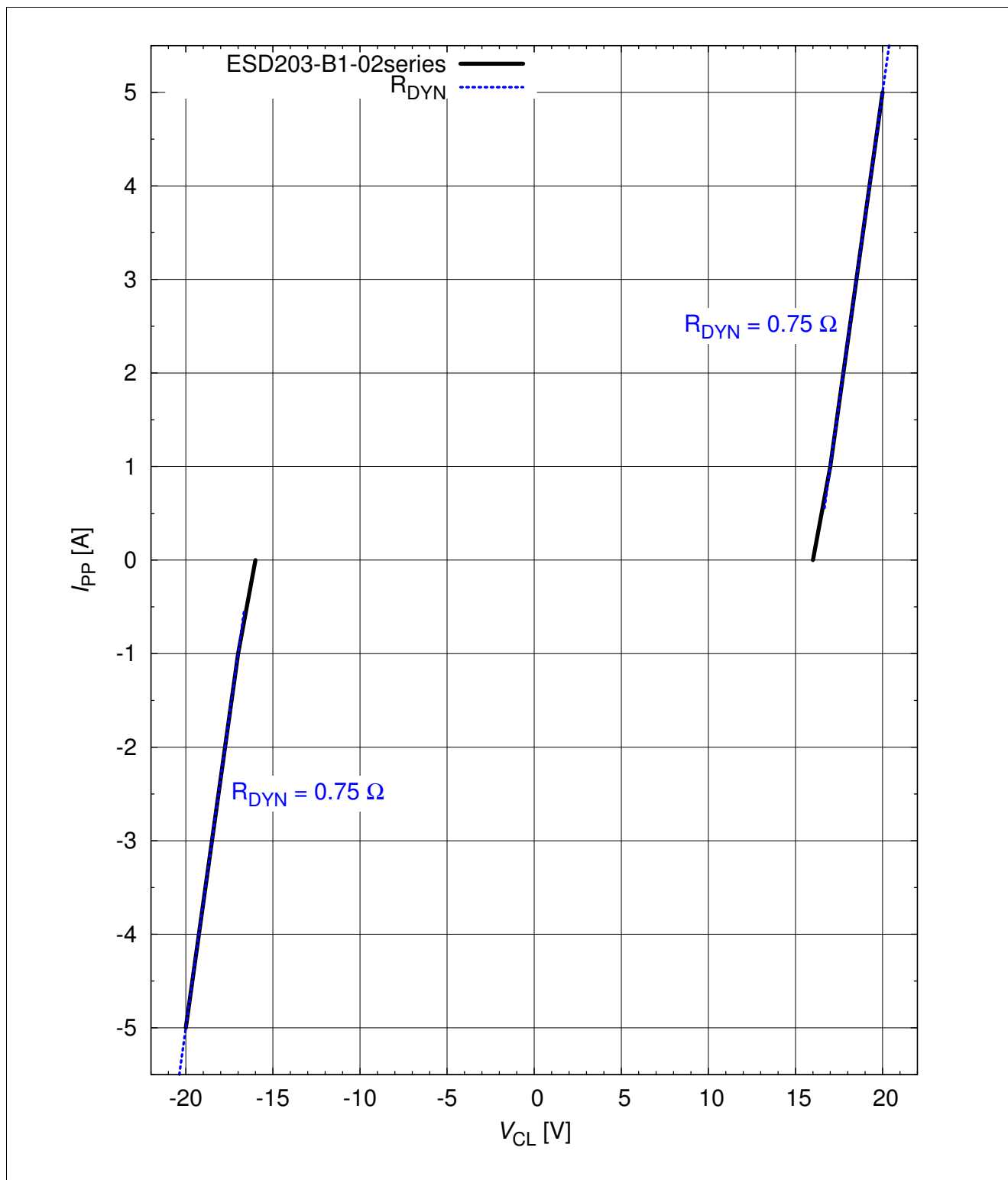


Figure 3-4 Pulse current (IEC61000-4-5) versus clamping voltage: $I_{PP} = f(V_{CL})$

Typical Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

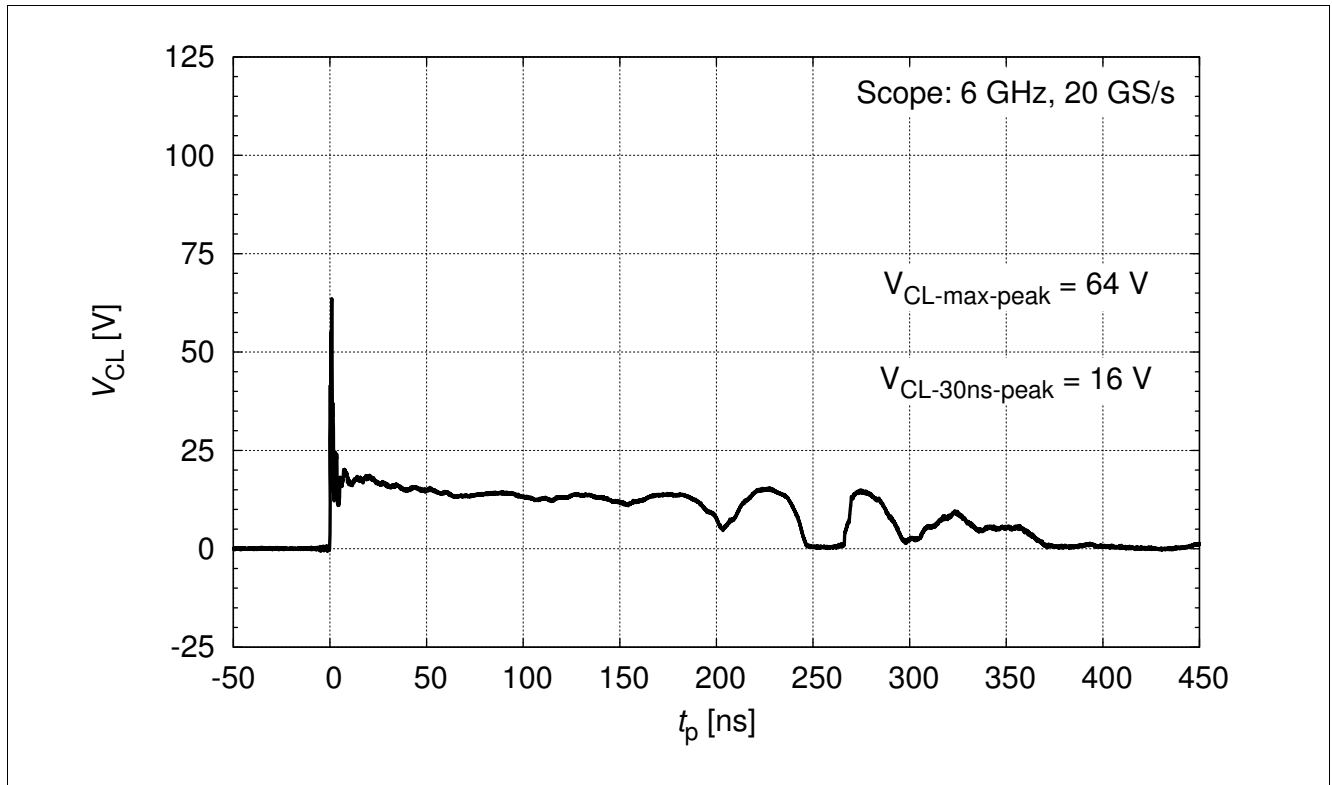


Figure 3-5 IEC61000-4-2 : $V_{CL} = f(t)$, 8 kV positive pulse from pin 1 to pin 2

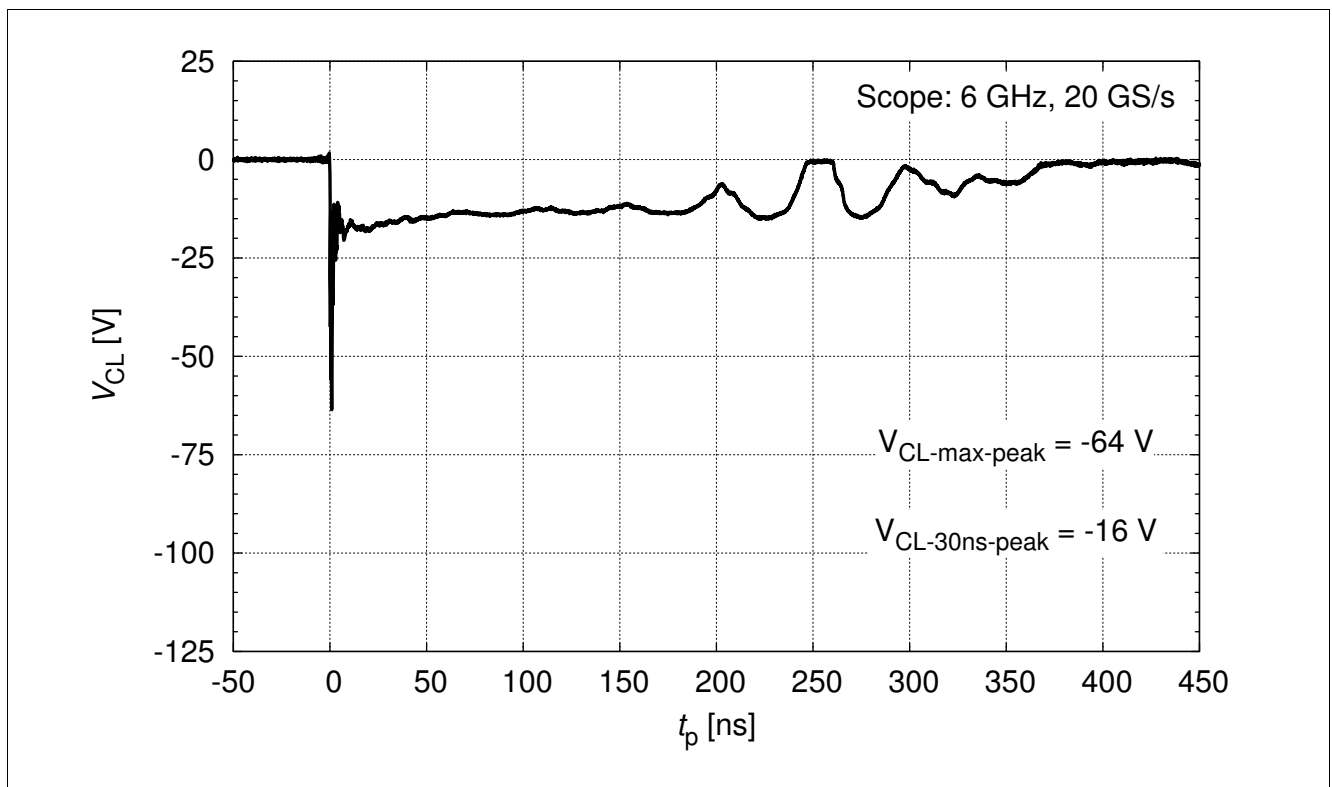


Figure 3-6 IEC61000-4-2 : $V_{CL} = f(t)$, 8 kV negative pulse from pin 1 to pin 2

Typical Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

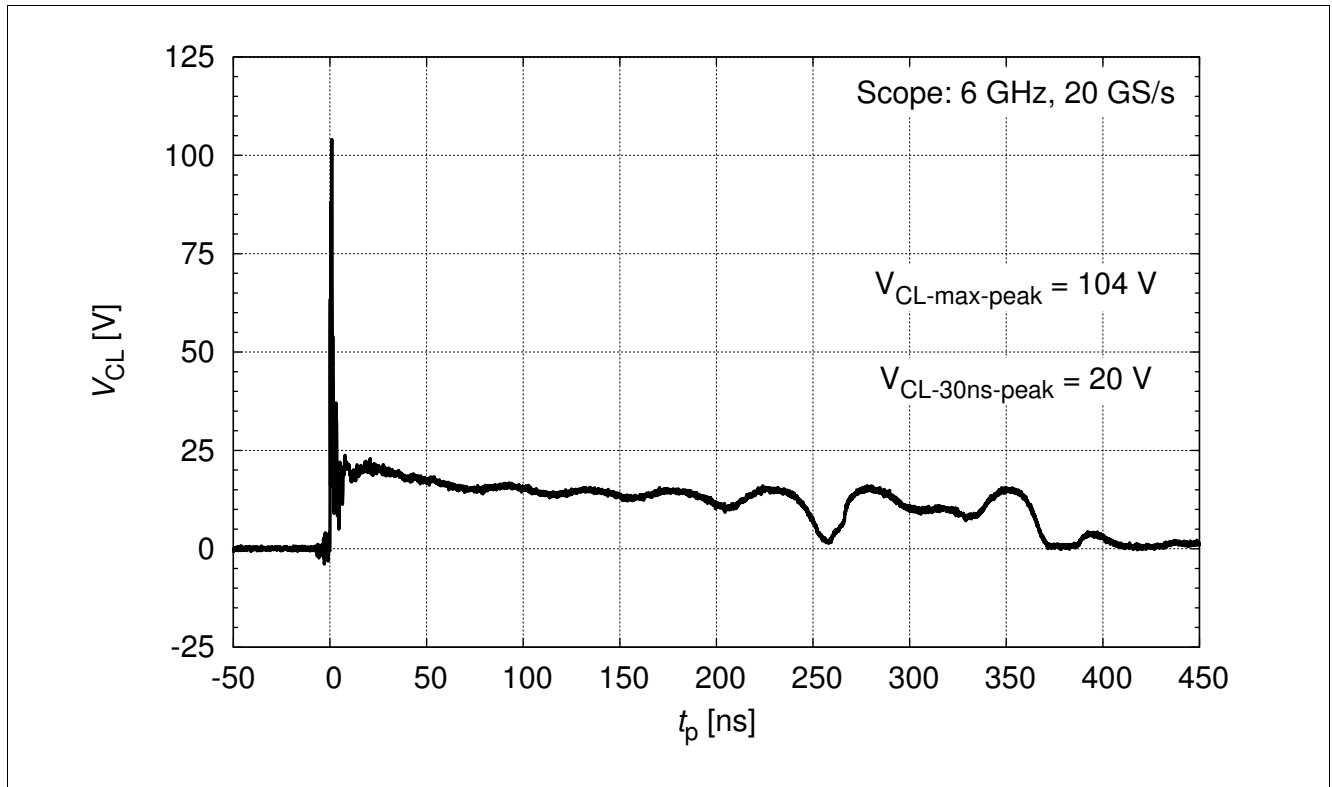


Figure 3-7 IEC61000-4-2 : $V_{CL} = f(t)$, 15 kV positive pulse from pin 1 to pin 2

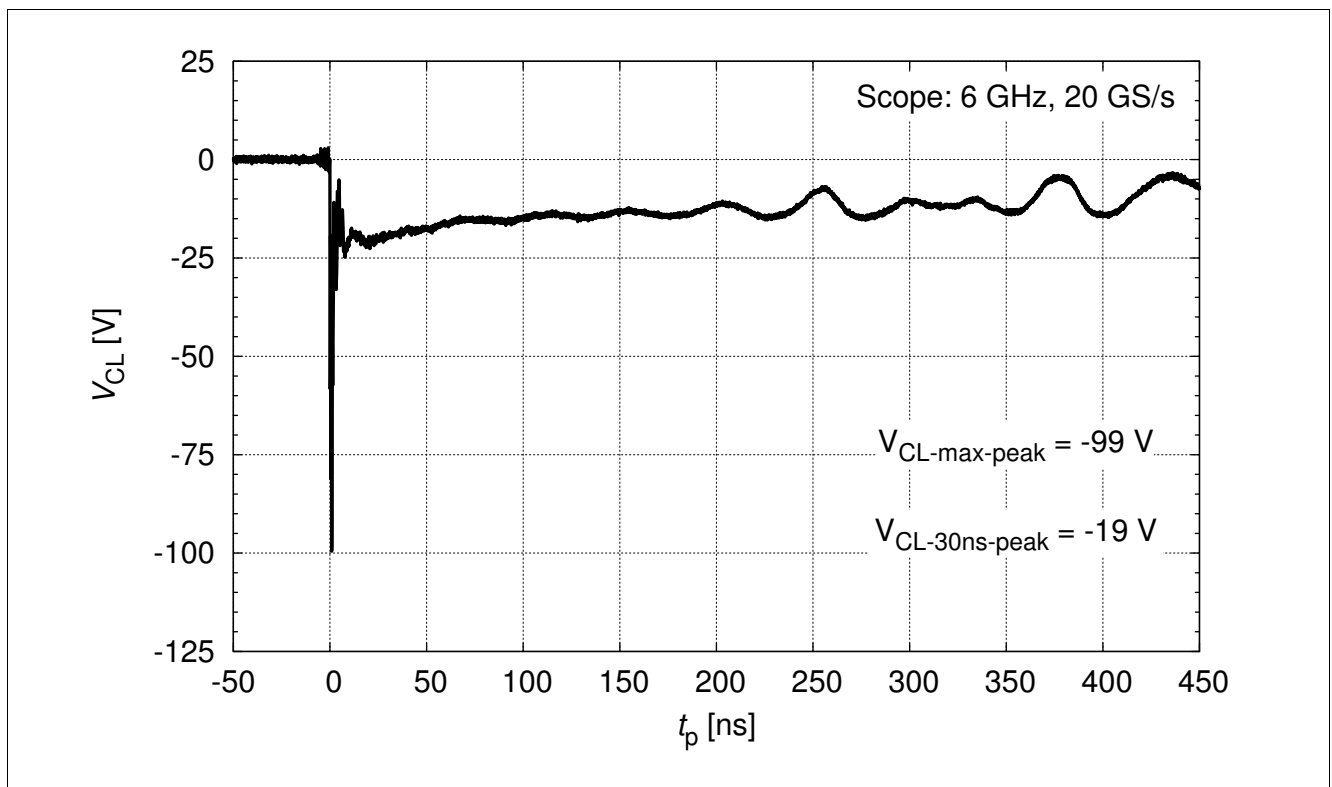


Figure 3-8 IEC61000-4-2 : $V_{CL} = f(t)$, 15 kV negative pulse from pin 1 to pin 2

4.2 TSLP-2-20

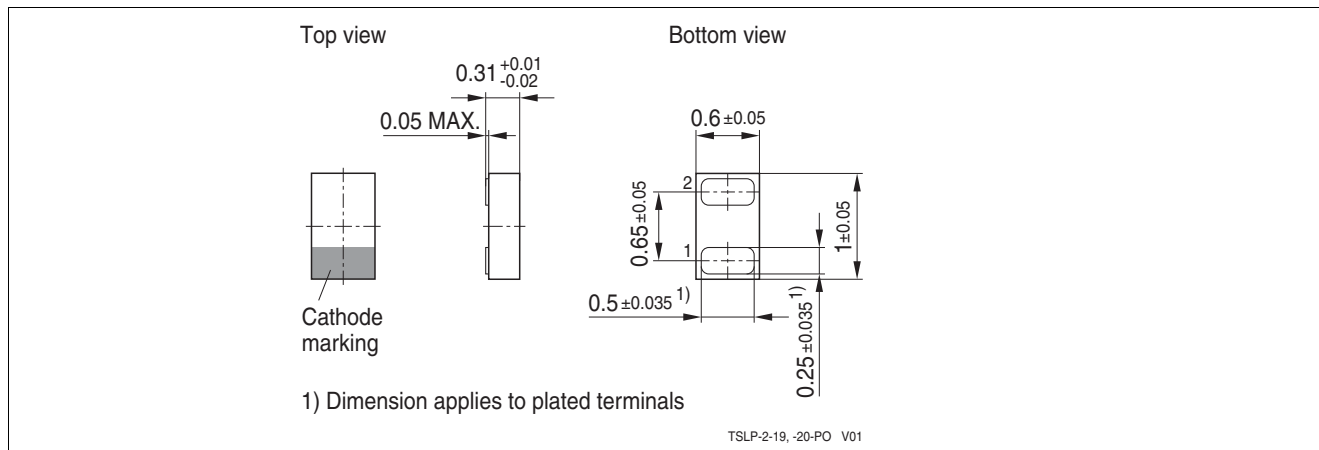


Figure 4-5 TSLP-2-20: Package outline(dimension in mm), proposal

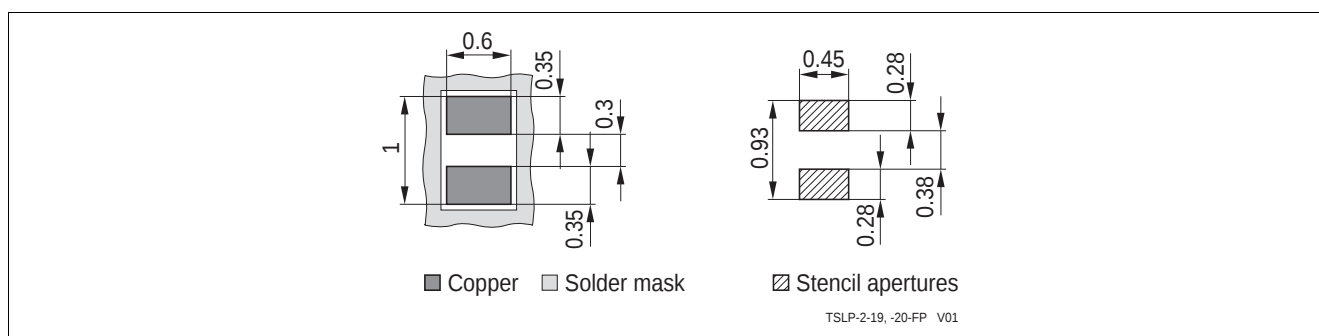


Figure 4-6 TSLP-2-20: Footprint (dimension in mm), proposal

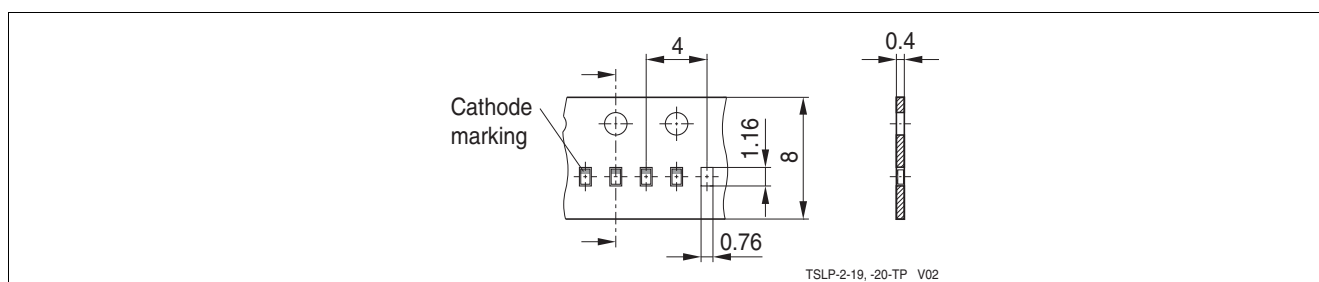


Figure 4-7 TSLP-2-20: Tape information (dimension in mm), proposal

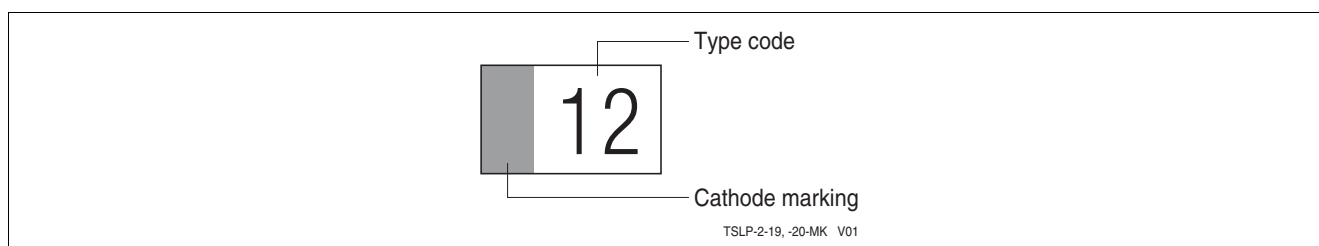


Figure 4-8 TSLP-2-20: Marking example

References

- [1] Infineon AG - **Application Note AN210**: Effective ESD Protection design at System Level Using VF-TLP Characterization Methodology

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